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Hori et al.

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(54) **SEMICONDUCTOR DEVICE**

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(73) Assignee: **Fuji Electric Co., Ltd.**, Kanagawa (JP)

(**) Term: **14 Years**

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(30) **Foreign Application Priority Data**

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(51) **LOC (9) Cl.** **13-03**

(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**
USPC D13/110, 182; D7/509, 608, 619.1, D7/624.1, 624.2; 257/668, 678, 690; 361/713, 361/728, 736, 752, 775; 324/754, 755, 765
See application file for complete search history.

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(57) **CLAIM**

The ornamental design for a semiconductor device, as shown and described.

DESCRIPTION

FIG. 1 is a front, top, right side perspective view of a semiconductor device showing our new design;

FIG. 2 is a front view thereof;

FIG. 3 is a rear view thereof;

FIG. 4 is a top plan view thereof;

FIG. 5 is a bottom plan view thereof;

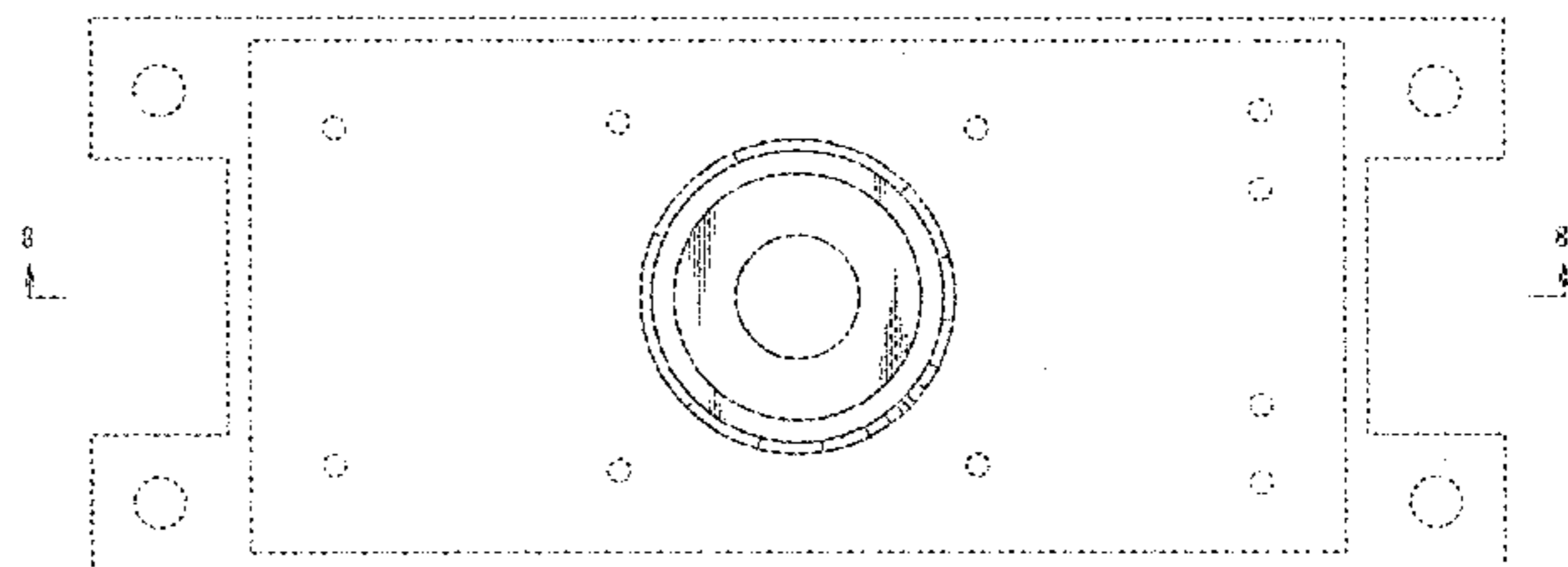
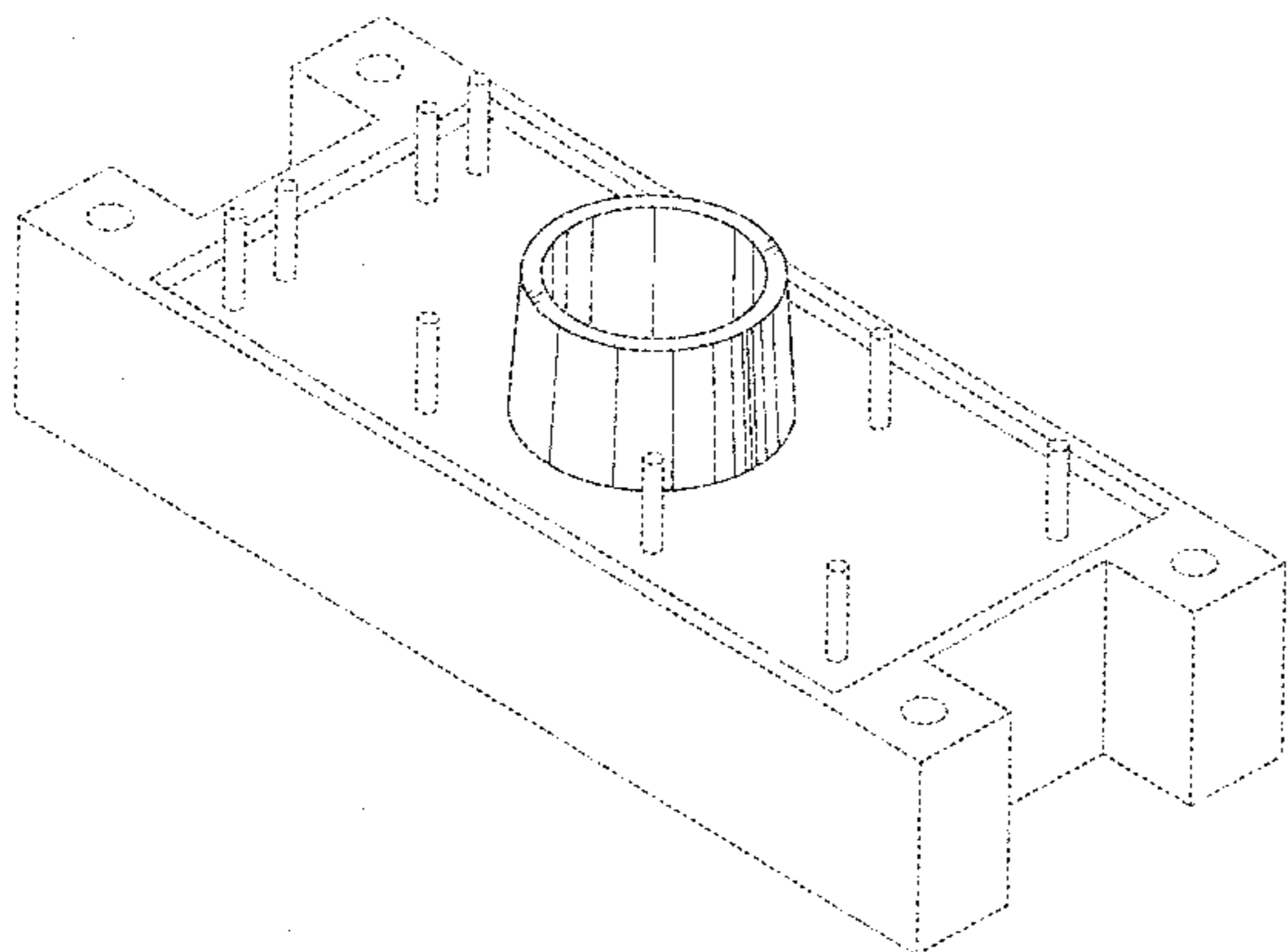
FIG. 6 is a left side view thereof;

FIG. 7 is a right side view thereof; and,

FIG. 8 is a cross sectional view taken along line 8-8 of FIG. 4.

The broken lines shown in the drawings represent portions of the semiconductor device that form no part of the claimed design.

1 Claim, 6 Drawing Sheets



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Fig. 1

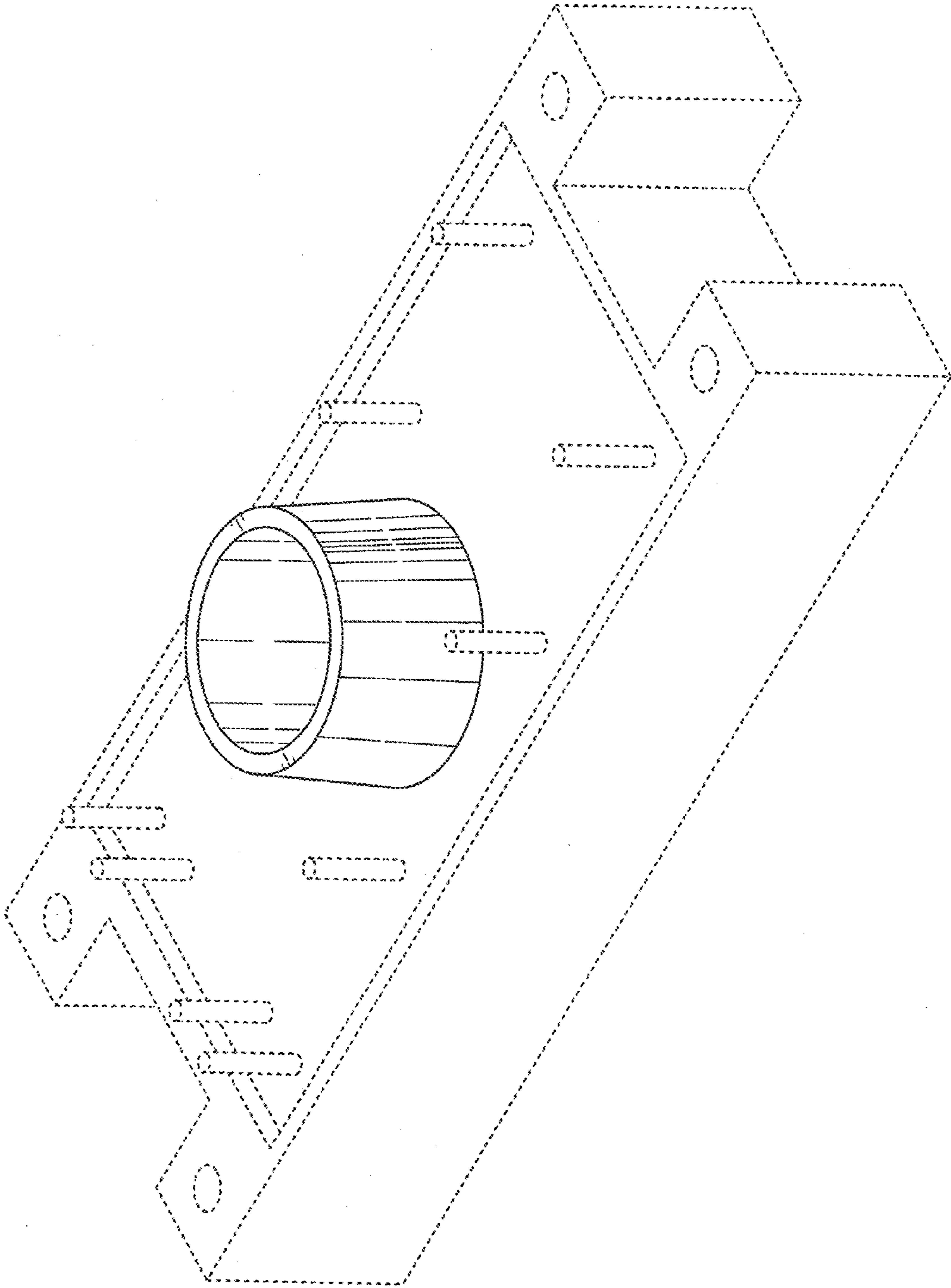


Fig. 2

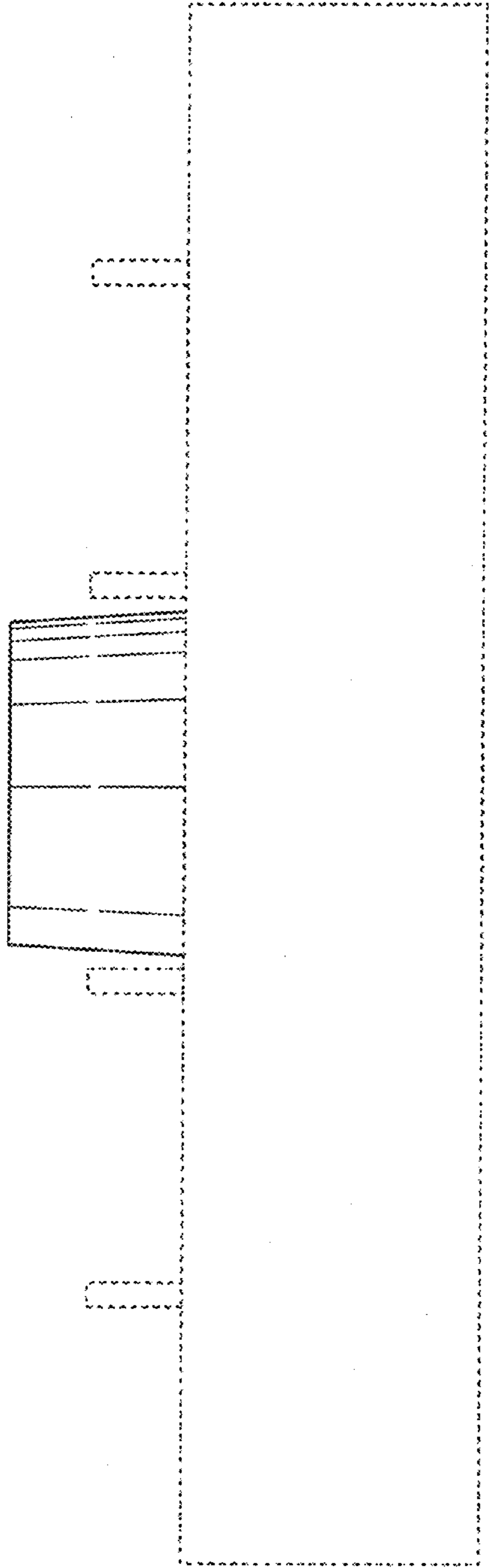


Fig. 3

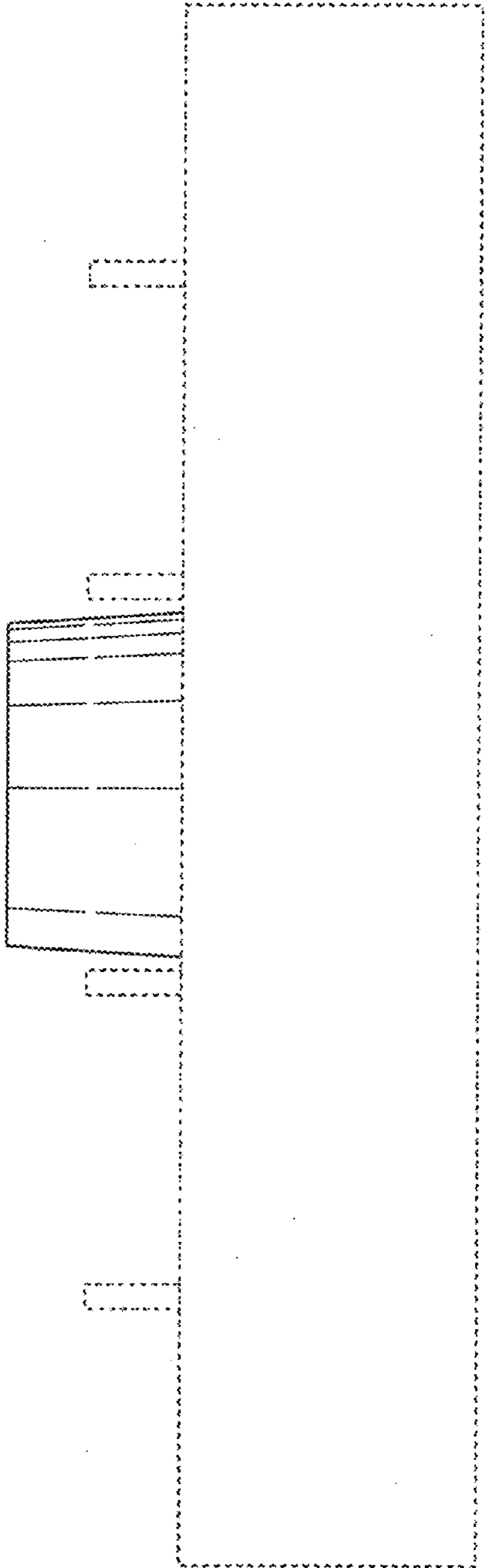


Fig. 4

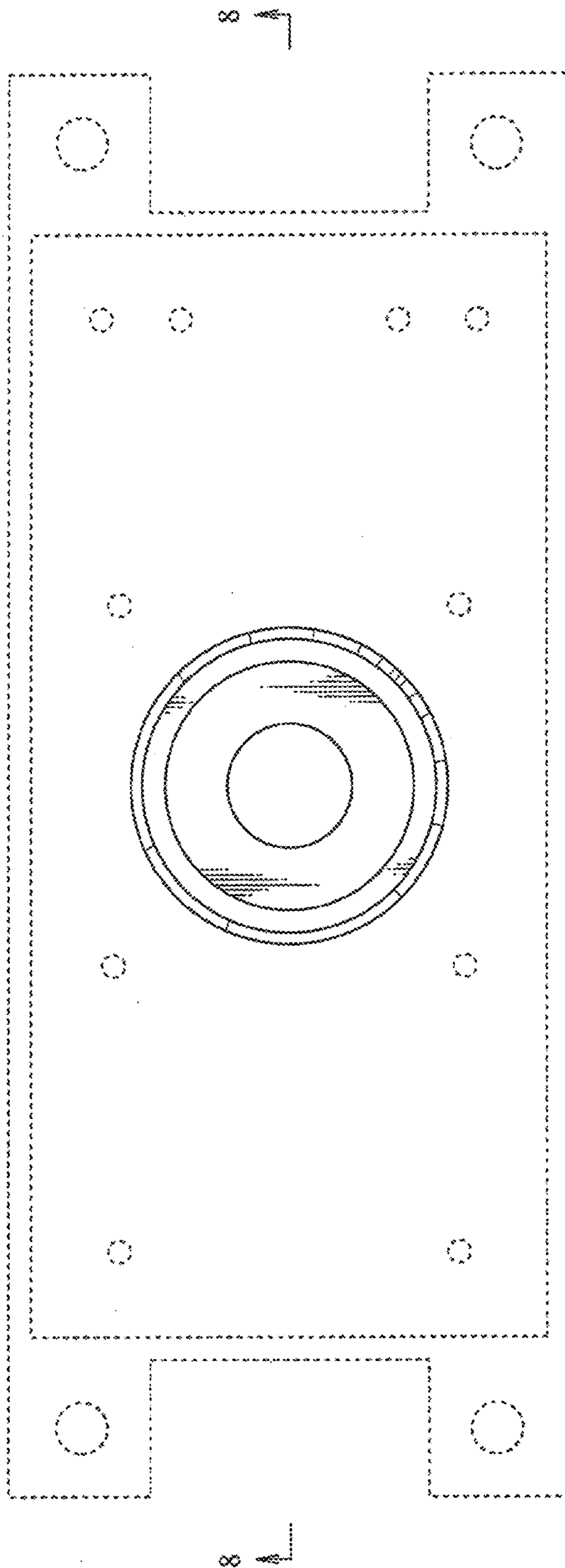


Fig. 5

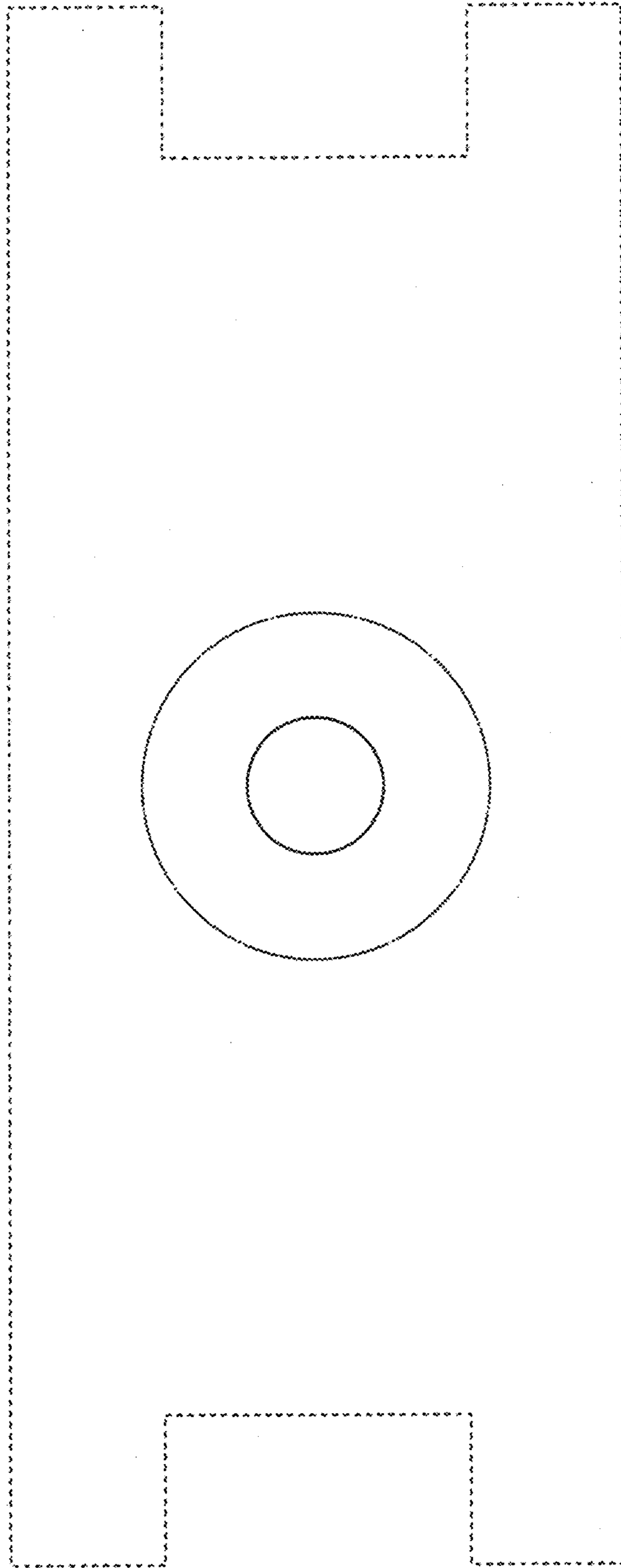


Fig. 7

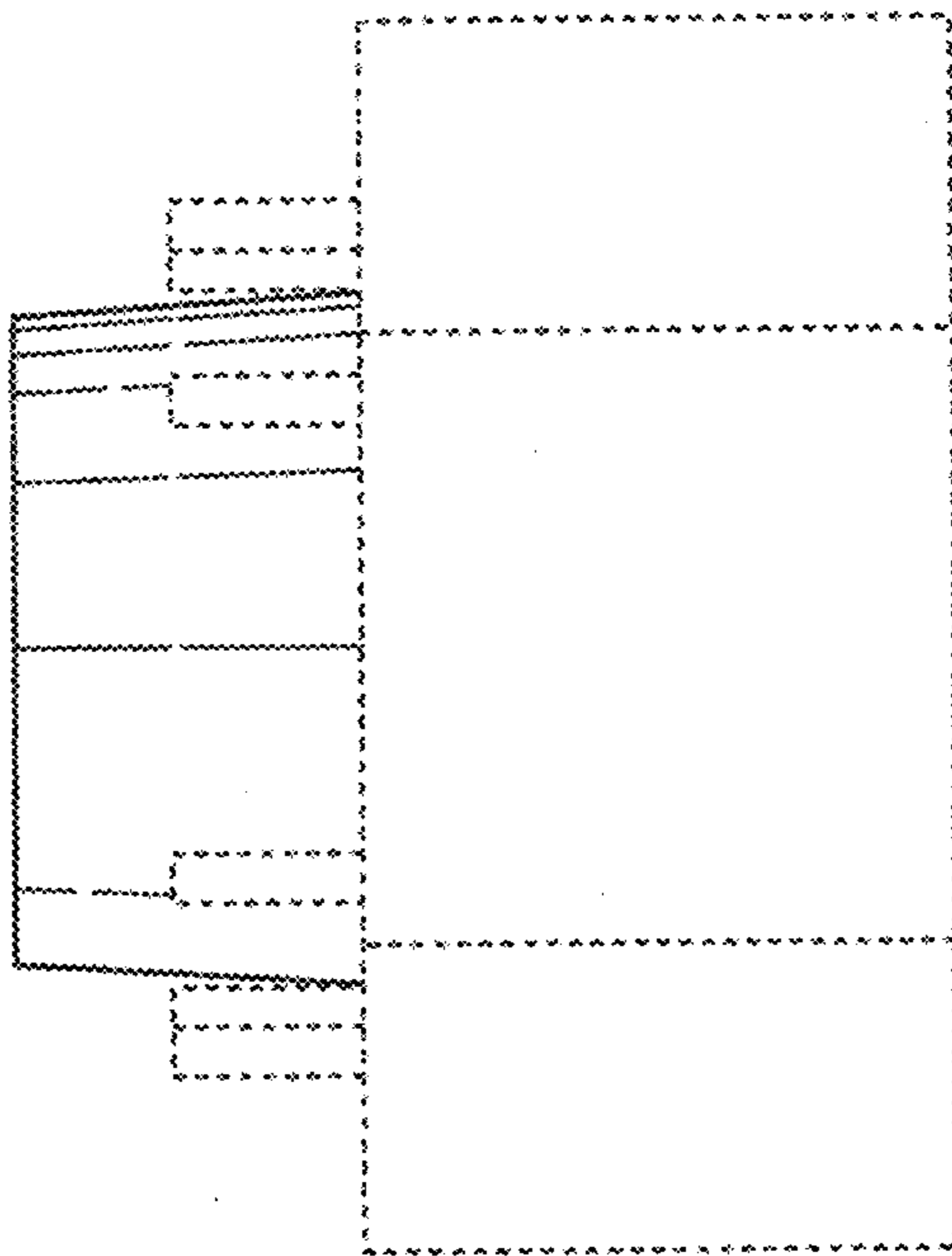


Fig. 6

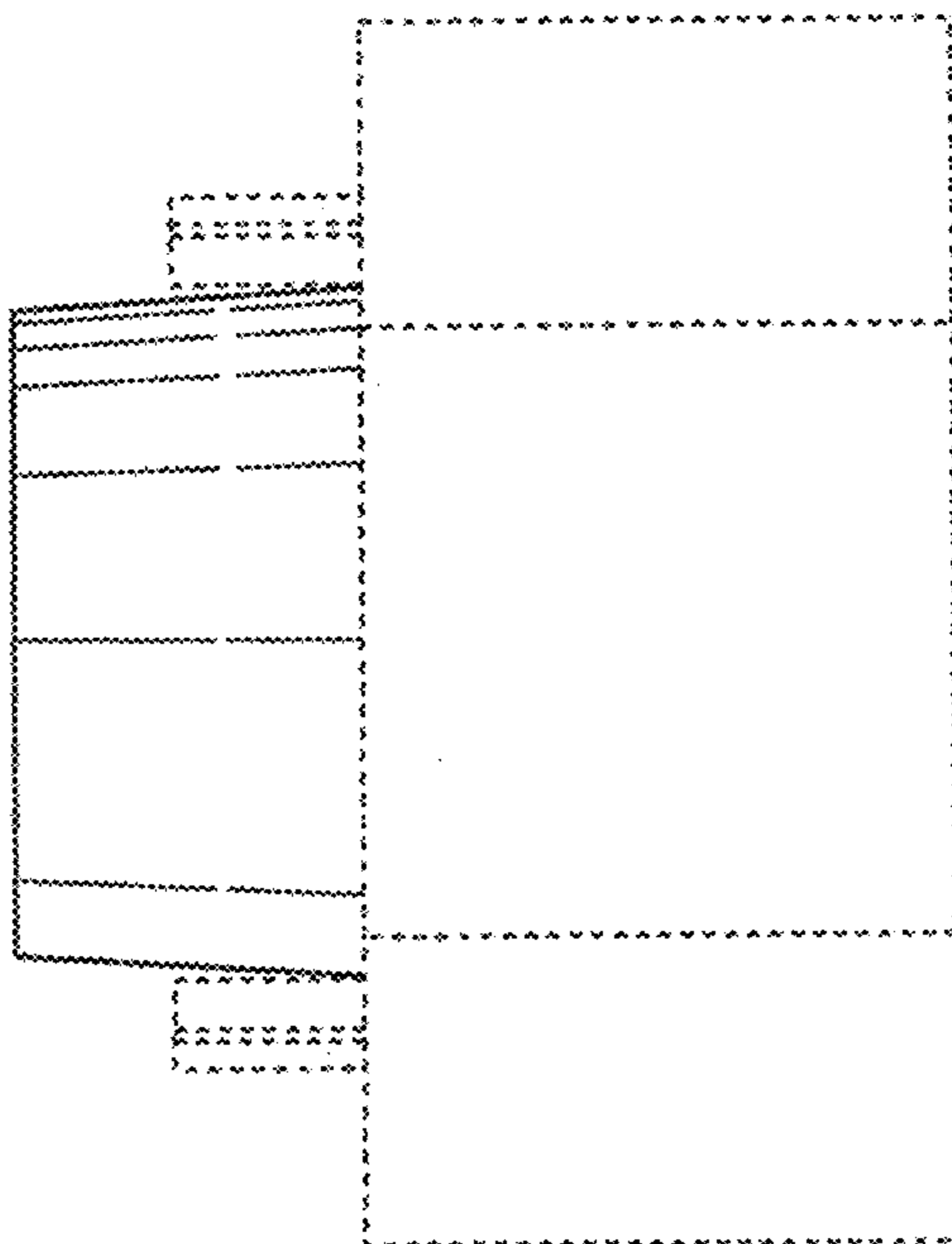


Fig. 8

